



DUAL N-CHANNEL ENHANCEMENT MODE MOSFET

Product Summary

| Device | BV _{DSS} | R _{DS(ON)} Max | I _D Max T _A = +25°C | |
|-----------|-------------------|--------------------------------|--|--|
| N-Channel | 12V | 150mΩ @ $V_{GS} = 4.5V$ | 2.0A | |
| | | 185mΩ @ V _{GS} = 2.5V | 1.8A | |

Features and Benefits

- Footprint of just 1.3 mm²
- Ultra-Low Profile Package 0.35mm Profile
- Low Gate Threshold Voltage
- Fast Switching Speed
- Ultra-Small Surface Mount Package
- ESD Protected Gate
- Totally Lead-Free & Fully RoHS Compliant (Notes 1 & 2)
- Halogen and Antimony Free. "Green" Device (Note 3)
- Qualified to AEC-Q101 Standards for High Reliability

Description and Applications

This MOSFET is designed to minimize the on-state resistance (R_{DS(ON)}), yet maintain superior switching performance, making it ideal for high efficiency power management applications.

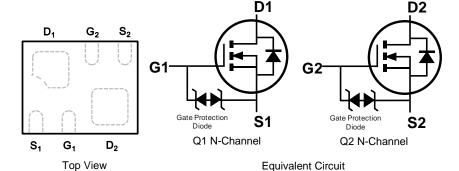
- Motor Control
- Power Management Functions
- Backlighting

Mechanical Data

- Case: X2-DFN1310-6 (Type B)
- Case Material: Molded Plastic, "Green" Molding Compound.
 UL Flammability Classification Rating 94V-0
- Moisture Sensitivity: Level 1 per J-STD-020
- Terminals: Finish NiPdAu Annealed over Copper Leadframe.
 Solderable per MIL-STD-202, Method 208 4
- Weight: 0.002 grams (Approximate)



Bottom View



Ordering Information (Note 4)

| Part Number | Reel Size (inches) | Tape Width (mm) | Quantity per Reel |
|---------------|--------------------|-----------------|-------------------|
| DMN1150UFL3-7 | 7 | 8 | 3.000 |

Pin-Out

Notes:

- 1. No purposely added lead. Fully EU Directive 2002/95/EC (RoHS) & 2011/65/EU (RoHS 2) compliant.
- See http://www.diodes.com/quality/lead_free.html for more information about Diodes Incorporated's definitions of Halogen- and Antimony-free, "Green" and Lead-free.
- 3. Halogen- and Antimony-free "Green" products are defined as those which contain <900ppm bromine, <900ppm chlorine (<1500ppm total Br + Cl) and <1000ppm antimony compounds.
- 4. For packaging details, go to our website at http://www.diodes.com/products/packages.html.

Marking Information

150

150 = Product Type Marking Code



Maximum Ratings (@T_A = +25°C, unless otherwise specified.)

| Characteristic | Symbol | Value | Unit | | |
|--|-----------------|--|----------------|------------|---|
| Drain-Source Voltage | V_{DSS} | 12 | V | | |
| Gate-Source Voltage | V_{GSS} | ±6 | V | | |
| Continuous Drain Current (Note 5) V _{GS} = 4.5V | Steady State | $T_A = +25^{\circ}C$ $T_A = +70^{\circ}C$ | I _D | 2.0 1.6 | А |

Thermal Characteristics (@T_A = +25°C, unless otherwise specified.)

| Characteristic | | Symbol | Value | Unit |
|--|------------------------|-------------------|-------------|------|
| Total Power Dissipation (Note 5) | T _A = +25°C | P_{D} | 0.39 | W |
| Thermal Resistance, Junction to Ambient (Note 5) | Steady State | R _{θJA} | 320 | °C/W |
| Total Power Dissipation (Note 6) | T _A = +25°C | P _D | 0.9 | W |
| Thermal Resistance, Junction to Ambient (Note 6) | Steady State | R _{θJA} | 141 | °C/W |
| Thermal Resistance, Junction to Case (Note 6) | · | R ₀ JC | 49 | C/VV |
| Operating and Storage Temperature Range | | $T_{J_i}T_{STG}$ | -55 to +150 | °C |

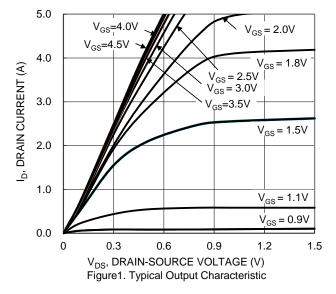
Electrical Characteristics (@T_A = +25°C, unless otherwise specified.)

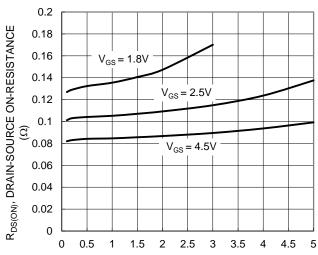
| Characteristic | Symbol | Min | Тур | Max | Unit | Test Condition | |
|--|---------------------|------|------|-----|------|--|--|
| OFF CHARACTERISTICS (Note 7) | | | | | | | |
| Drain-Source Breakdown Voltage | BV _{DSS} | 12 | _ | _ | V | $V_{GS} = 0V, I_D = 250\mu A$ | |
| Zero Gate Voltage Drain Current T _J = +25°C | I _{DSS} | _ | 1 | 1 | μΑ | $V_{DS} = 12V, V_{GS} = 0V$ | |
| Gate-Source Leakage | I_{GSS} | _ | - | ±10 | μΑ | $V_{GS} = \pm 6V$, $V_{DS} = 0V$ | |
| ON CHARACTERISTICS (Note 7) | | | | | | | |
| Gate Threshold Voltage | V _{GS(TH)} | 0.35 | 0.42 | 1.0 | V | $V_{DS} = V_{GS}, I_{D} = 250 \mu A$ | |
| | | | 119 | 150 | | VGS = 4.5V, ID = 1A | |
| Static Drain-Source On-Resistance | R _{DS(ON)} | _ | 141 | 185 | mΩ | VGS = 2.5V, ID = 1A | |
| | , , | | 175 | 210 | | VGS = 1.8V, ID = 1A | |
| Diode Forward Voltage | V_{SD} | _ | 0.7 | 1.2 | V | $V_{GS} = 0V, I_{S} = 150mA$ | |
| DYNAMIC CHARACTERISTICS (Note 8) | | | | | | | |
| Input Capacitance | C _{ISS} | _ | 115 | | pF | V 0V V 0V | |
| Output Capacitance | Coss | _ | 25 | | pF | $V_{DS} = 6V, V_{GS} = 0V,$ -f = 1.0MHz | |
| Reverse Transfer Capacitance | C _{RSS} | _ | 23 | | pF | 1 = 1.0101112 | |
| Gate Resistance | R _G | _ | 90 | | Ω | $V_{DS} = 0V$, $V_{GS} = 0V$, $f = 1MHz$ | |
| Total Gate Charge | Q_{G} | _ | 1.4 | | nC | | |
| Gate-Source Charge | Q_{GS} | _ | 0.1 | _ | nC | $V_{DS} = 4V, V_{GS} = 4.5V, I_{D} = 1A$ | |
| Gate-Drain Charge | Q_{GD} | _ | 0.1 | _ | nC | | |
| Turn-On Delay Time | t _{D(ON)} | _ | 4.0 | | ns | | |
| Turn-On Rise Time | t _R | _ | 7.4 | _ | ns | $V_{GS} = 6V$, $V_{DS} = 4V$, | |
| Turn-Off Delay Time | t _{D(OFF)} | _ | 44 | - | ns | $R_G = 1\Omega$, $I_D = 1A$ | |
| Turn-Off Fall Time | t _F | _ | 19 | | ns | | |

 Device mounted on FR-4 substrate PC board, 2oz copper, with minimum recommended pad layout.
 Device mounted on FR-4 substrate PC board, 2oz copper, with 1inch square copper plate.
 Short duration pulse test used to minimize self-heating effect. Notes:

^{8.} Guaranteed by design. Not subject to product testing.







I_D, DRAIN-SOURCE CURRENT (A) Figure 3. Typical On-Resistance vs. Drain Current and Gate Voltage

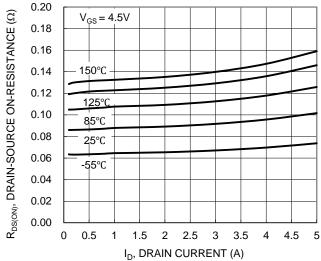


Figure 5. Typical On-Resistance vs. Drain Current and Temperature

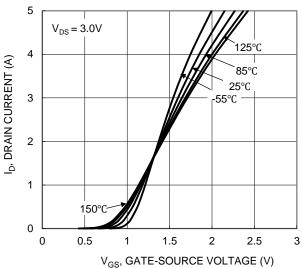


Figure 2. Typical Transfer Characteristic

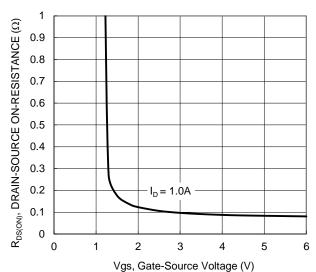


Figure 4. Typical Transfer Characteristic

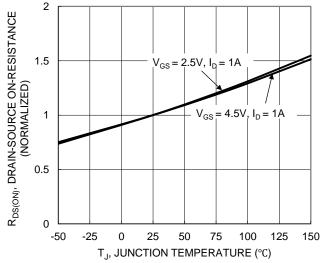


Figure 6. On-Resistance Variation with Temperature



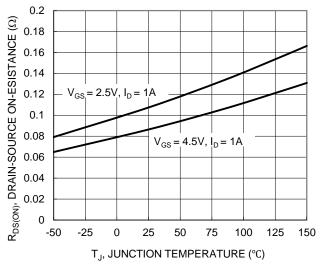
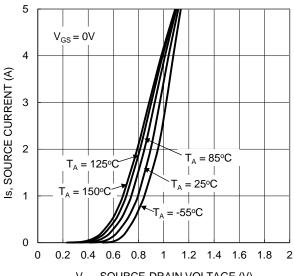


Figure 7. On-Resistance Variation with Temperature



V_{SD}, SOURCE-DRAIN VOLTAGE (V) Figure 9. Diode Forward Voltage vs. Current

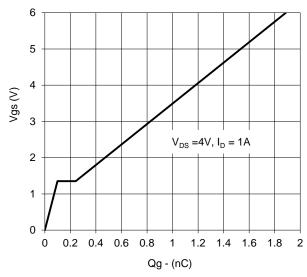


Figure 11. Gate Charge

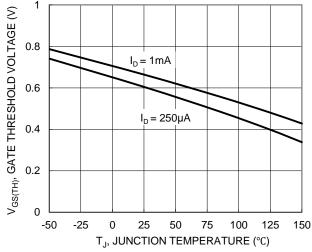
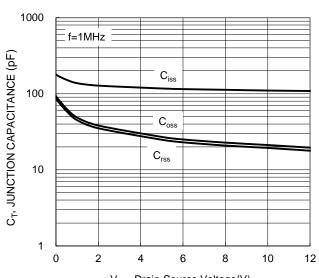


Figure 8. Gate Threshold Variation vs. junction Temperature



 V_{DS} , Drain-Source Voltage(V) Figure 10. Typical Junction Capacitance

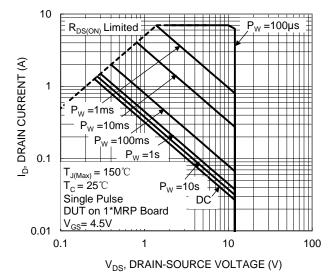


Figure 12. SOA, Safe Operation Area



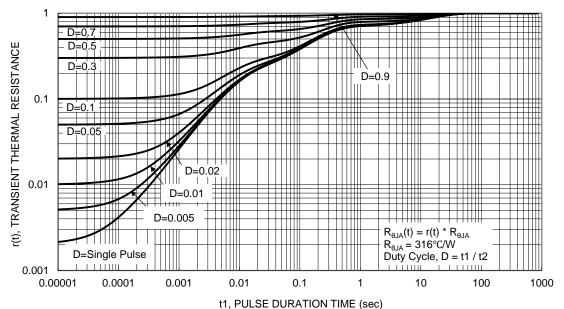


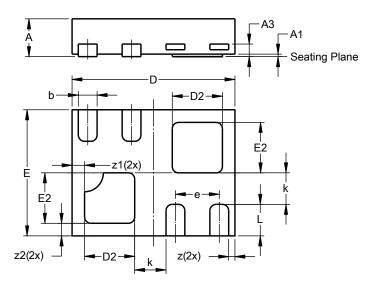
Figure 13. Transient Thermal Resistance



Package Outline Dimensions

Please see http://www.diodes.com/package-outlines.html for the latest version.

X2-DFN1310-6 (Type B)

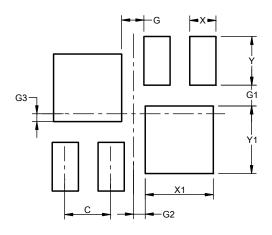


| X2-DFN1310-6 | | | | | | |
|----------------------|------|------|-------|--|--|--|
| (Type B) | | | | | | |
| Dim | Min | Max | Тур | | | |
| Α | 0.25 | 0.35 | 0.30 | | | |
| A1 | 0 | 0.05 | 0.02 | | | |
| А3 | | | 0.100 | | | |
| b | 0.10 | 0.20 | 0.15 | | | |
| D | 1.25 | 1.35 | 1.30 | | | |
| D2 | 0.30 | 0.50 | 0.40 | | | |
| Е | 0.95 | 1.05 | 1.00 | | | |
| E2 | 0.30 | 0.50 | 0.40 | | | |
| е | | | 0.35 | | | |
| k | 0.15 | | | | | |
| L | 0.20 | 0.30 | 0.25 | | | |
| Z | | | 0.05 | | | |
| z1 | | | 0.10 | | | |
| z2 | | | 0.10 | | | |
| All Dimensions in mm | | | | | | |

Suggested Pad Layout

Please see http://www.diodes.com/package-outlines.html for the latest version.

X2-DFN1310-6 (Type B)



| Dimensions | Value (in mm) | | | |
|------------|------------------|--|--|--|
| С | 0.350 | | | |
| G | 0.17 | | | |
| G1 | 0.16 | | | |
| G2 | 0.09 | | | |
| G3 | 0.06 | | | |
| X | 0.20 | | | |
| X1 | 0.52 | | | |
| Y | 0.375 | | | |
| Y1 | 0.52 | | | |



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